LDMOS S-Band radar pallet amplifier

Rev. 01 — 28 May 2010

**Objective data sheet** 

### 1. Product profile

### 1.1 General description

200 W LDMOS amplifier pallet intended for radar applications in the 2.9 GHz to 3.3 GHz range.

#### Table 1. Typical performance

RF performance at  $T_{case} = 25 \ ^{\circ}C$  in a common source class-AB test circuit.

Mode of operation	f	V <sub>DS</sub>	P <sub>L(1dB)</sub>	G <sub>p</sub>	η <sub>D</sub>	I <sub>Dq</sub>
	(GHz)	(V)	(W)	(dB)	(%)	(mA)
class-AB; $t_p$ = 300 $\mu s;$ $\delta$ = 10 %	2.9 to 3.3	32	220	11	45	100

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- Excellent thermal stability
- Designed for broadband operation (2.9 GHz to 3.3 GHz)
- Matched to 50 Ω for ease of use
- Extreme low weight pallet (environmental friendly and easy to use)

### 1.3 Applications

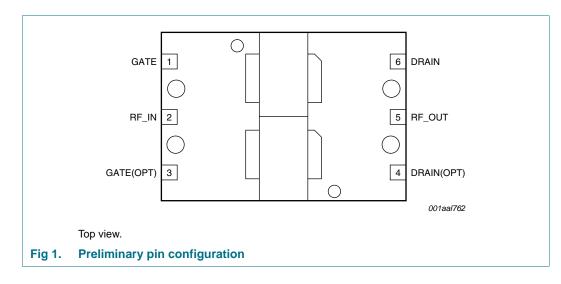
General S-Band radar applications



LDMOS S-Band radar pallet amplifier

## 2. Pinning information

### 2.1 Pinning



### 2.2 Pin description

Table 2.	Pin description <sup>[1]</sup>	1
Symbol	Pin	Description
GATE	1	gate
RF_IN	2	RF input
GATE(OPT	Г) З	optional gate
DRAIN(OF	PT) 4	optional drain
RF_OUT	5	RF output
DRAIN	6	drain

[1] The case is a source/ground connection.

## 3. Ordering information

Table 3. Orderin	Table 3. Ordering information										
Type number Package											
	Name	Description	Version								
BLS6G2933P-200	-	<tbd></tbd>	<tbd></tbd>								

BLS6G2933P-200

LDMOS S-Band radar pallet amplifier

### 4. Limiting values

Table 4.         Limiting values           In accordance with the Absolute Maximum Rating System (IEC 60134).											
Symbol	Parameter	Conditions	Min	Max	Unit						
V <sub>DS</sub>	drain-source voltage		-	60	V						
V <sub>GS</sub>	gate-source voltage		-	±11	V						
I <sub>D</sub>	drain current		-	66	А						
T <sub>stg</sub>	storage temperature		-40	+125	°C						
Tj	junction temperature		-	200	°C						

## 5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
Z <sub>th(j-h)</sub>	transient thermal impedance from	$T_h = 25 \text{ °C}; P_L = 200 \text{ W}$		
	junction to heatsink	$t_p$ = 300 $\mu$ s; $\delta$ = 10 %	[ <u>1]</u> <tbd></tbd>	K/W
		$t_p$ = 200 $\mu$ s; $\delta$ = 10 %	[ <u>1]</u> <tbd></tbd>	K/W
		$t_p$ = 100 $\mu$ s; $\delta$ = 10 %	[ <u>1]</u> <tbd></tbd>	K/W

[1] Measured from junction to heatsink of the pallet.

## 6. Characteristics

#### Table 6. Characteristics per section

 $T_i = 25 \ ^{\circ}C$ ; unless otherwise specified.

,	· ·					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS}$ = 0 V; $I_D$ = 1 mA	60	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; I <sub>D</sub> = 360 mA	1.4	1.8	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS}$ = 0 V; $V_{DS}$ = 28 V	-	-	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = ±11 V; $V_{DS}$ = 0 V	-	-	900	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 10 A	-	13	-	S

BLS6G2933P-200

#### LDMOS S-Band radar pallet amplifier

## 7. Application information

#### Table 7. Application information

RF performance in common source class-AB circuit;  $T_h = 25$  °C;  $t_p = 300 \ \mu$ s;  $\delta = 10 \%$ ;  $I_{Da} = 100 \ m$ A;  $P_L = 215 \ W$ ;  $Z_{th} = < tbd > K/W$ ; unless otherwise specified.

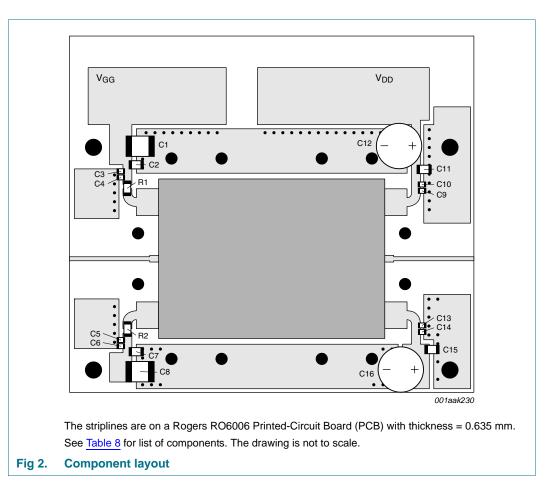
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	frequency		2.9	-	3.3	GHz
V <sub>CC</sub>	supply voltage		-	-	32	V
t <sub>p</sub>	pulse duration		-	-	300	μS
δ	duty cycle		-	10	-	%
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		-	220	-	W
G <sub>p</sub>	power gain		10	11	-	dB
η <sub>D</sub>	drain efficiency		40	45	-	%
P <sub>droop(pulse)</sub>	pulse droop power		-	0.1	0.3	dB
Z <sub>i</sub>	input impedance		-	50	-	Ω
Zo	output impedance		-	50	-	Ω
IRL	input return loss		-	-10	-	dB

### 7.1 Ruggedness in class-AB operation

The BLS6G2933P-200 is capable of withstanding a load mismatch corresponding to VSWR = 5 : 1 through all phases under the following conditions:  $V_{DS}$  = 32 V;  $I_{Dq}$  = 100 mA;  $P_L$  = 215 W pulsed;  $t_p$  = 300 µs;  $\delta$  = 10 %.

LDMOS S-Band radar pallet amplifier

## 8. Test information



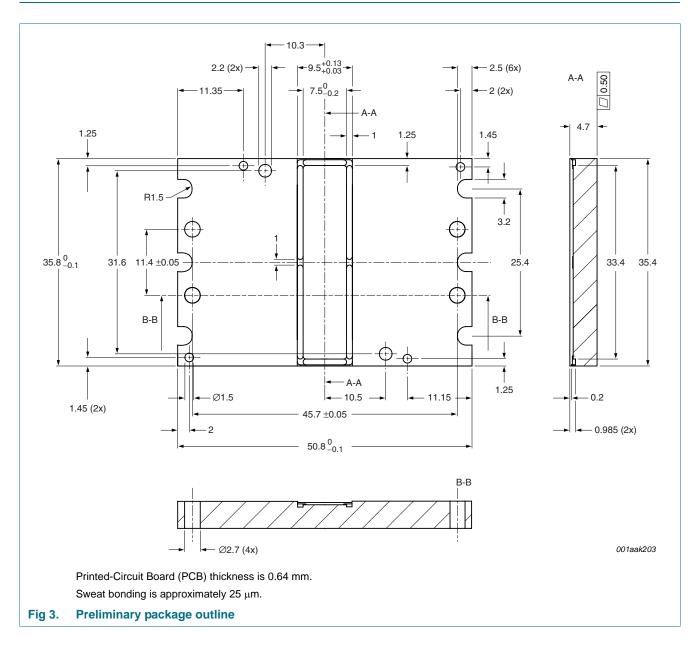
## Table 8.List of componentsSee Figure 2 for component layout.

See <u>Figure 2</u> for component layout.			
Component	Description	Value	Remarks
C1, C8	multilayer ceramic chip capacitor	47 μF	TDK
C2, C7, C11, C15	multilayer ceramic chip capacitor	100 pF	ATC100B
C3, C4, C5, C6, C9, C10, C13, C14	multilayer ceramic chip capacitor	33 pF	ATC100A
C12	electrolytic capacitor	680 μF	
C16	electrolytic capacitor	68 μF	
R1, R2	SMD resistor	33 Ω	thin film

BLS6G2933P-200

LDMOS S-Band radar pallet amplifier

## 9. Package information



LDMOS S-Band radar pallet amplifier

## 10. Package outline

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#### Fig 4. Package outline

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LDMOS S-Band radar pallet amplifier

## **11. Abbreviations**

Table 9.	Abbreviations
Acronym	Description
LDMOS	Laterally Diffused Metal Oxide Semiconductor
RF	Radio Frequency
S-Band	Short wave Band
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

## **12. Revision history**

Table 10. Revision history											
Document ID	Release date	Data sheet status	Change notice	Supersedes							
BLS6G2933P-200 v.1	20100528	Objective data sheet	-	-							

BLS6G2933P-200

LDMOS S-Band radar pallet amplifier

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BLS6G2933P-200

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9 of 11

#### LDMOS S-Band radar pallet amplifier

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BLS6G2933P-200

**Objective data sheet** 

#### LDMOS S-Band radar pallet amplifier

## **15. Contents**

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
2	Pinning information 2
2.1	Pinning
2.2	Pin description 2
3	Ordering information 2
4	Limiting values 3
5	Thermal characteristics 3
6	Characteristics 3
7	Application information 4
7.1	Ruggedness in class-AB operation 4
8	Test information 5
9	Package information 6
10	Package outline 7
11	Abbreviations 8
12	Revision history 8
13	Legal information 9
13.1	Data sheet status 9
13.2	Definitions
13.3	Disclaimers 9
13.4	Trademarks 10
14	Contact information 10
15	Contents 11

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